

CLAIMS:

1. A thin film capacitor comprising a carrier substrate (1), at least two interdigitated electrodes (4, 5), and at least one dielectric (3), characterized in that at least one interdigitated electrode (4) is arranged below the dielectric (3) and at least one interdigitated electrode (5) is arranged above the dielectric (3).

2. A thin film capacitor as claimed in claim 1, characterized in that the interdigitated electrode (5) above the dielectric (3) is positioned in a staggered arrangement with respect to the interdigitated electrode (4) below the dielectric (3).

3. A thin film capacitor as claimed in claim 1, characterized in that the dielectric (3) comprises a plurality of layers.

4. A thin film capacitor as claimed in claim 1, characterized in that the dielectric (3) comprises a ferroelectric ceramic material.

5. A thin film capacitor as claimed in claim 1, characterized in that a barrier layer (2) is provided on the carrier substrate (1).